



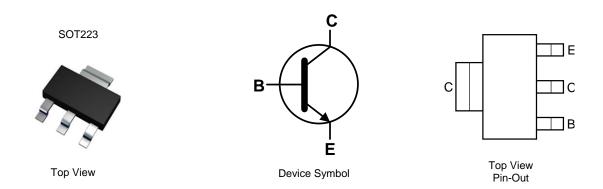
300V NPN MEDIUM POWER HIGH VOLTAGE TRANSISTOR IN SOT223

#### Features

- BV<sub>CEO</sub> > 300V
- BV<sub>CBO</sub> > 300V
- I<sub>C</sub> = 0.5A High Continuous Current
- I<sub>CM</sub> = 1A Peak Pulse Current
- Complementary PNP Type: FZT757
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



#### Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT657TA	AEC-Q101	FZT657	7	12	1,000
FZT657QTA	Automotive	FZT657	7	12	1,000

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

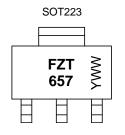
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally

the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

Notes:



FZT 657 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 8 = 2018) WW or  $\overline{W}W$  = Week Code (01 to 53)



# Absolute Maximum Ratings ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	0.5	A
Peak Pulse Current	I <sub>CM</sub>	1	A

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		3.0	
Power Dissipation	(Note 7)	D	2.0	w
	(Note 8)	PD	1.6	vv
	(Note 9)		1.2	
	(Note 6)		41.7	
Thermal Resistance, Junction to Ambient	(Note 7)		62.5	
mermar Resistance, Junction to Amblent	(Note 8)	R <sub>θJA</sub>	78.1	°C/W
	(Note 9)		104	
Thermal Resistance Junction to Lead (Note 10)		R <sub>θJL</sub>	12.9	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 11)

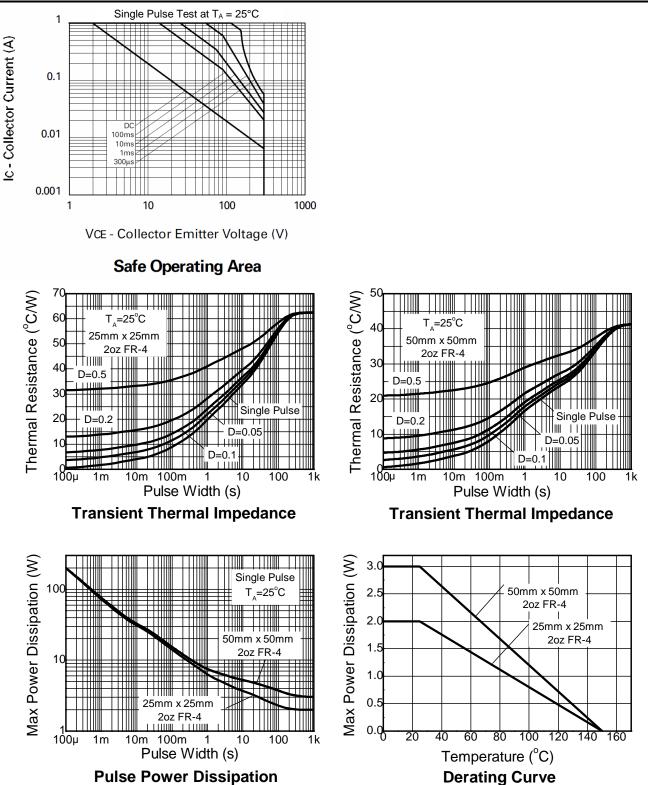
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a still air conditions whilst operating in a steady-state.
Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
Same as Note 6, except the device is mounted on minimum recommended pad layout.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### FZT657

#### Thermal Characteristics and Derating Information





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

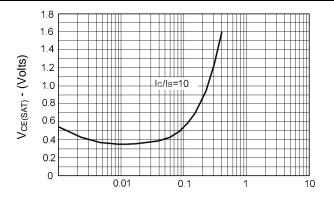
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	300	_	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV <sub>CEO</sub>	300	_	—	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	—	—	V	I <sub>E</sub> = 100μA
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	—	100	nA	V <sub>CB</sub> = 200V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 5.6V$
DC Current Gain (Note 12)	h <sub>FE</sub>	40 50	_		_	$I_{C} = 10mA, V_{CE} = 5V$ $I_{C} = 100mA, V_{CE} = 5V$
Collector-Emitter Saturation Voltage (Note 12)	V <sub>CE(SAT)</sub>	_	_	0.5	V	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA
Base-Emitter Saturation Voltage (Note 12)	V <sub>BE(SAT)</sub>	_	_	1.0	V	$I_{\rm C} = 100 {\rm mA}, I_{\rm B} = 10 {\rm mA}$
Base-Emitter Turn-On Voltage (Note 12)	V <sub>BE(ON)</sub>	_	_	1.0	V	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 5V
Output Capacitance	C <sub>OBO</sub>	_	_	20	pF	$V_{CB} = 20V$ , f = 1MHz
Current Gain-Bandwidth Product	f⊤	30	—	—	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 20MHz

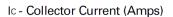
Note: 12. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



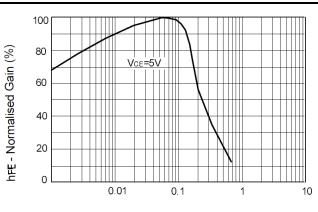
FZT657

#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



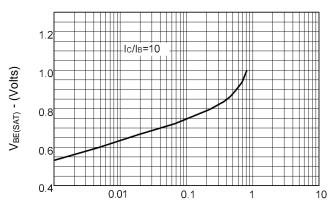






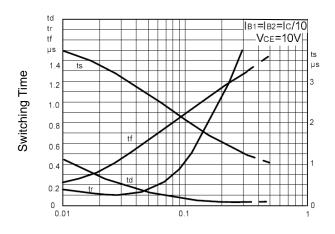


hFE v IC



Ic - Collector Current (Amps)

V<sub>BE(SAT)</sub> v I<sub>C</sub>



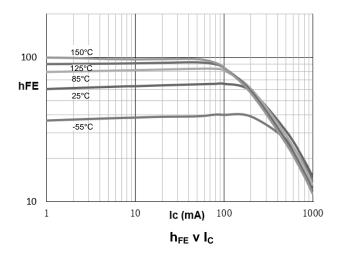
Ic - Collector Current (Amps)

# **Switching Speeds**

(s) (s)

I<sub>C</sub> - Collector Current (Amps)

 $V_{BE(ON)} v I_C$ 



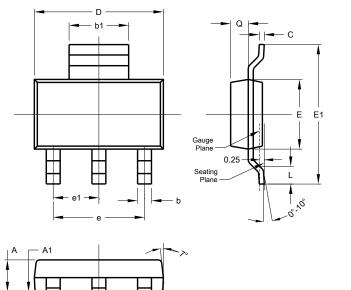


**FZT657** 

## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

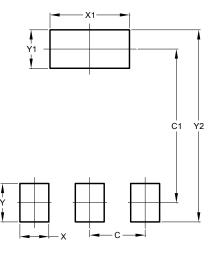


	SOT223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
E	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All I	All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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